

Highlights

Dynamics of Light Localization via Coherent Control: The Interplay of Transmission, Absorption and Disorder in Photonic Crystals

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- Active tuning of absorption, Lyapunov exponents (quantifying confinement stability), and localization regimes via coherent interactions, combining refractive index randomness with Λ -atom doping in a defect layer.
- Contrast in band-gap localization, where absorption enhances confinement (disrupted by disorder) and band-edge localization, where disorder boosts light trapping but absorption weakens it.

Dynamics of Light Localization via Coherent Control: The Interplay of Transmission, Absorption and Disorder in Photonic Crystals

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Abstract

This study examines the dynamic relationship between the Lyapunov exponent, absorption, and structural disorder to exploit localization phenomena in photonic crystals. We study systems where random variations in the refractive index of one of the bilayers introduce disorder, while a defect layer features non-uniform doping with Λ -type atoms and enables coherent modulation of effective refractive index. The coherent control permits the active tuning of absorption, Lyapunov exponent, and localization characteristics in disordered regimes. A striking contrast in the absorption and Lyapunov spectra is observed for band gap and band edge frequencies, highlighting distinct localization behaviors. These findings advance understanding of light-matter interactions and field localization in disordered systems, offering pathways for tailored photonic devices.

Keywords: Disordered photonic crystals, Lyapunov exponents, Dynamic Localization, Absorption, Λ - type three-level atomic doping, Anderson localization.

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1. Introduction

The localization of light in Photonic Crystals (PCs) arises when structural irregularities trap light waves, disrupting their normal propagation and reducing their spread over large distances [1]. Yablonovitch's seminal work revealed that three-dimensional periodic dielectric structures with photonic band gaps can suppress spontaneous emission by preventing radiative transitions within the gap [2]. Further research proposed that carefully designed disorder in 3D dielectric superlattices could achieve controlled photon localization in lossless systems, leveraging deliberate randomness rather than energy dissipation to confine light effectively [3]. In disordered PCs, Lyapunov exponent (LE) is usual marker of the exponential decay of the amplitude of light waves propagating through the structure due to interference caused by disorder. They are associated with the inverse of the localization length and are critical to understanding wave transport phenomena, including Anderson localization. In PCs, the localization length tends to be greater in the propagating regions and lower in the gap regions, leading to the formation of wave functions that are confined to limited spatial confines. The applications of LE is not without constraints and their limitations can impact the interpretation and reliability of results in certain scenarios [4]. Researchers have exploited the effects of disorder in refractive indices in 1D PCs to quantitatively tailor the localization and delocalization of light within the photonic bandgap and their associated passbands [5]. Studies on PCs have combined experimental and computational approaches to analyze how controlled structural disorders both correlated and uncorrelated affect their optical properties [6, 7, 8, 9, 10, 11]. Experimental work has also examined linear and nonlinear wave propagation, slow light transport, and angle-dependent effects in disordered 1D waveguide arrays, demonstrating realizations of the Anderson Model [12, 13, 14, 15, 16]. Research has also shown with the LE dynamics that when disorder surpasses a critical threshold, states from pass bands and band edges exhibit single parameter scaling behavior but states from mid bandgap deviate from this behavior [17]. Subsequent studies have predicted distinct localization regimes in such disordered photonic crystals [18]. In such systems, wave decay can occur due to various phenomena, including localization, inelastic scattering, and out-of-plane losses. Numerical experiments and theoretical proofs have shown that absorption does not provide a cutoff length similar to an inelastic scattering length for renormalization of wave transport in a multiply scattering medium [19]. For band edge frequencies,

the presence of an electromagnetic mobility edge has been demonstrated, characterized by an unusual increase in absorption due to localization fluctuations in photon diffusivity within a disordered medium, as the critical frequency is approached [20, 21].

Our research primarily focused on numerically investigating the coherent control of LE in both bandgap and band edge regions for a selected range of defect layer width. The coherent control is achieved by non-uniform doping of central defect layer with Λ type atoms. This incorporation induces specific atomic transitions that facilitate the manipulation of effective refractive index of the crystal, thereby enabling precise control over light propagation within the crystal. The structural disorder in the crystal is introduced via random variations in the refractive index of one of the bilayers. To demonstrate the properties of PC, we have employed the conventional transfer matrix approach. We analyze the dynamics of LE and observe that a narrow region of minimum localization length exists for gap as well as band frequencies. Further, we examine the impact of dissipation/absorption caused by the defect layer containing three-level atoms/losses. Our observations reveal that the effect of absorption on localization for the band gap and band edge frequencies is different which has not been reported earlier. In addition, coherent control of mobility edge can be achieved for band edge frequencies. This control persists irrespective of the amount of disorder in PC. However, for highly disordered crystals, distinguishing between band gap and band pass frequencies becomes unclear. In addition, our system demonstrates that both gap and band frequencies are sensitive to losses in contrast to [22] in which it is shown that gap frequencies are independent of losses. Hence, we investigate light localization under the combined influence of absorption, LE, and structural disorder. Our findings highlight that Anderson localization induced by disorder becomes more pronounced at band edge frequencies, whereas disorder suppresses localization in defect modes. Within the bandgap region, the resonance between atomic transitions and the defect modes enhances the localization in the defect layer due to absorption. In contrast, at band edge frequencies, high absorption diminishes localization within the defect layer, underscoring the contrasting effects of absorption in these regions.

It is important to note that the use of PCs is predominantly confined to the visible and near-infrared regions of the electromagnetic spectrum. We emphasize that disordered PCs offer distinct advantages compared to their ordered counterparts. The advancements and trends in PCs demonstrate their potential in integrated photonics, sensing, biosensing and biomedicine with

particular emphasis on drug delivery, blood detection, and tumor screening [23, 24, 25]. In our study, the wavelengths under consideration are confined to the visible to near-infrared spectrum. As the disorder in the analysis is uncorrelated and considering effective inhomogeneity of medium, the structural randomness can improve the selectivity of biosensors.

This paper is organized as follows: In section 2, we introduce Lyapunov exponent and absorption using Transfer matrix method. In section 3, we present numerical results to demonstrate the localization dynamics with the combined effects of disorder, Lyapunov exponent and absorption. Finally, we conclude the article in section 4.

2. Model

A PC of length L is considered such that A and B are the alternative layers with corresponding refractive indices n_A , n_B and $\lambda_0/4n_i, i \in A, B$, $\lambda_0 = 632.8nm$ their optical thicknesses, respectively. In the middle there is a defect layer D with refractive index $n_D = 2.1$ such that the configuration is of the form $((AB)^n)D((BA)^n)$. A control field with rabi frequency $2G$ is applied. The refractive indices of A layers are made random such that $n_{A_i} = n_A + \delta_j$, δ_j is the Gaussian distribution function given as $\frac{1}{2\pi\sigma} e^{-\frac{(x_i-\mu)^2}{2\sigma^2}}$, where $x_i = X[rand_i(0, 1)]$ are random numbers and σ , μ are standard deviation and mean of x_i 's respectively. Random parameter X ($= 10, 5, 2.5, 1.25$) governs the variation ranges of δ_j from 0 to 0.05, 0.12, 0.20, 0.42) where higher X reduces randomness. The refractive index $n_A = 2.22$ is fixed, while n_{A_i} varies randomly across A_i layers. The defect layer is doped with a three-level Λ type atomic system. The susceptibility of the doped three level atoms is of the form reported in[26]. The transfer matrix for entire system is $M = M_{A_1}M_B M_{A_2}M_B \dots \dots M_{A_{N-1}}M_B M_{A_N}$ The matrix for single layer is taken as in [26]. The transmission T , reflection R , and absorption A from left to right through crystal using elements of transfer matrix are $T = M_{11} - \frac{M_{12}M_{21}}{M_{22}}$, $R = \frac{-M_{12}}{M_{22}}$ and $A = 1 - (R + T)$ respectively. For a long enough system $n \in \infty$, the LE is given as $L(\omega) = -\frac{1}{n} \langle \ln T \rangle$ which is an averaged quantity over several random configurations.

3. Results and Discussions

3.1. Effect of Control field and disorder on Lyapunov exponent and absorption

We numerically explore the dependence of the LE on the defect layer width, d_D and control field G in disordered PCs. The LE inversely correlates with the penetration length, which is lower for the band gap region and decreases as the frequency approaches from edge to the band gap center. In this analysis, we have considered LE ensemble averaged over 16 random configurations. Our findings show that, for frequencies within the band gap of disordered PC, LE exhibits maximum values for a narrow range of control field while remaining lower yet non-zero across the entire examined range [Fig.1(a)]. Unlike prior studies, our results demonstrate that the control field and defect layer properties have a pronounced effect on regions with low penetration length (high LE) within the band gap frequencies [Fig.1(a)]. This effect leads to enhanced surface localization, suggesting that back scattering remains dominant in this region due to destructive interference. While for the region lying outside the red region [Fig.1(a)], LE has lower values such that penetration length is raised to reach enough probe field upto defect layer to induce atom-field interactions. The atomic doping of the defect layer leads to the emergence of a number of defect states in this region. These states enhance wave propagation through a mechanism akin to resonant tunneling. Hence, the possibility of field to be localized at the defect modes is increased at specific defect layer widths to induce atom field resonance. For band edge frequencies, LE exhibits a similar trend but amplitude gets smaller as compared to gap region due to the presence of higher density of states [Fig.1(b)]. It means that most of the probe field will be propagated through crystal. Additionally, increasing detuning (from 1γ to 5γ) only shifts the red region to higher G values, reflecting the role of detuning in modifying the resonance conditions and destructive interference leading to back scattering in the PC, while not affecting LE amplitude. Further, the variation of real and imaginary components of refractive index of defect layer are shown in [Fig.1(c)]. It is observed that for the mentioned narrow region in LE spectra, imaginary component of the refractive index of the defect layer gets maximized. These variations justify the alterations in overall transmission and hence LE of the crystal. Hence, the coherent control in LE spectra is attributed to the modifications in the refractive index of the doped defect layer and consequently of the PC. The band gap region in PCs is usually accompanied by smaller

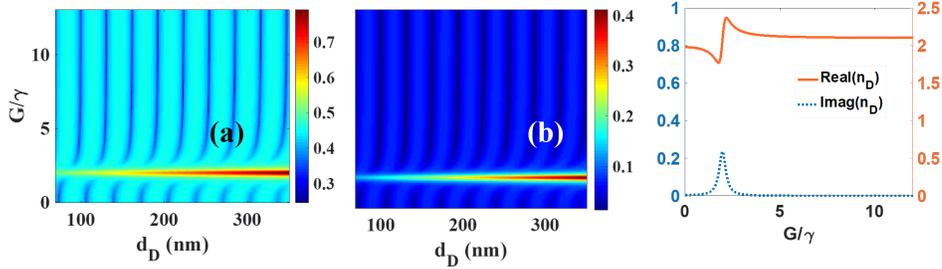


Figure 1: Lyapunov spectra with control field, $\frac{G}{\gamma}$ and defect layer width d_D at $X = 10$ (a) for defect mode, $\omega = 2.3036 \times 10^{15} Hz$ (b) for band edge mode, $\omega = 2.2789 \times 10^{15} Hz$ (c) variation of real(solid curve) and imaginary(dashed curve) components of n_D with $\frac{G}{\gamma}$, for $(2n + 1)$ layers, $n = 36$, $\gamma = 1 MHz$. Lyapunov spectra with control field, $\frac{G}{\gamma}$ and defect layer width d_D at $X = 10$ (a) for defect mode, $\omega = 2.3036 \times 10^{15} Hz$ (b) for band edge mode, $\omega = 2.2789 \times 10^{15} Hz$ (c) variation of real(solid curve) and imaginary(dashed curve) components of n_D with $\frac{G}{\gamma}$, for $(2n + 1)$ layers, $n = 36$, $\gamma = 1 MHz$.

absorption because most of the field is backscattered due to destructive interference caused by crystal's periodicity. We observe that because of the presence of the defect layer, a number of defect modes arise as the control field modifies the refractive index of the defect layer. These modes are accompanied with the field confinement and small spots of highly absorbed trapping light (marked in yellow ring in [Fig.2(a)-(c)]). These highlighted absorption hot spots indicate the resonance of doped atoms with the defect modes in the disordered cavity. This is probably due to the strong interaction between the localized electromagnetic field and atomic transitions when the defect mode confines light to a small region, significantly increasing local field intensity. Since light is confined and cannot escape due to bandgap, localized field interacts more efficiently with the absorbing medium, reinforcing the localization effect. The absorption is minimal in regions with high LE values because the field is not sufficient to interact with atoms. Inset in Fig.2(e) displays high-resolution absorption plot corresponding to the atomic resonance with defect mode [Fig.2(b)]. In contrast, the behaviour of absorption reverses for band edge frequencies corresponding to a narrow range of control field (for which LE is maximum) as shown in [Fig.3(a)-(c)]. Absorption gets maximum at the band edges due to enhanced photonic density of states (DOS). On the other hand, it is minimum in other regions where the overlap between the atomic transitions and band edge modes is reduced. This might happen due

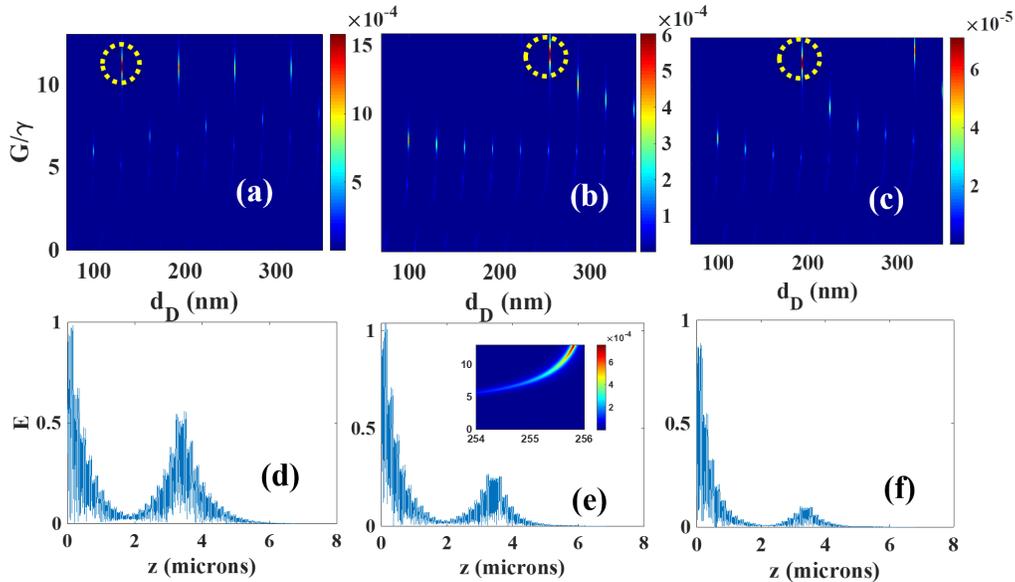


Figure 2: Absorption spectra as a function of control field, $\frac{G}{\gamma}$ and defect layer width d_D for defect mode for different randomness parameter (a) $X = 10$ at $\omega = 2.3036 \times 10^{15} Hz$ (b) $X = 5$ at $\omega = 2.2874 \times 10^{15} Hz$ (c) $X = 2.5$ at $\omega = 2.2772 \times 10^{15} Hz$ and field profiles along crystal axis, z respectively for $(2n + 1)$ layers, $n = 36$ corresponding to (a), (b) and (c) respectively for region marked in yellow ring, (d) $G = 11.0683\gamma$, $d_D = 130.7229nm$, (e) $G = 11.7588\gamma$, $d_D = 255.7286nm$, and (f) $G = 11.4322\gamma$, $d_D = 193.8191nm$. The inset in (e) represents the resonance mode in higher resolution corresponding to (b).

to saturation effects at high DOS, where the atomic transitions become saturated, leading to reduced probe field interaction despite the high DOS. This coherent control of absorption at band edges enables the manipulation of electromagnetic mobility edge accompanied with high absorption and refers to a transition point separating localized electromagnetic modes (immobile) from extended modes (mobile) in a disordered or periodic medium [20]. The induced defect modes in bandgap are affected by introducing random variations in the refractive index in PC while the absorption in gap does not follow a universal trend in the presence of randomness. Moreover, in the band edge, absorption is minimally affected and the trend remains robust against the amount of disorder considered. Hence, the coherent control of absorption is maintained in PC.

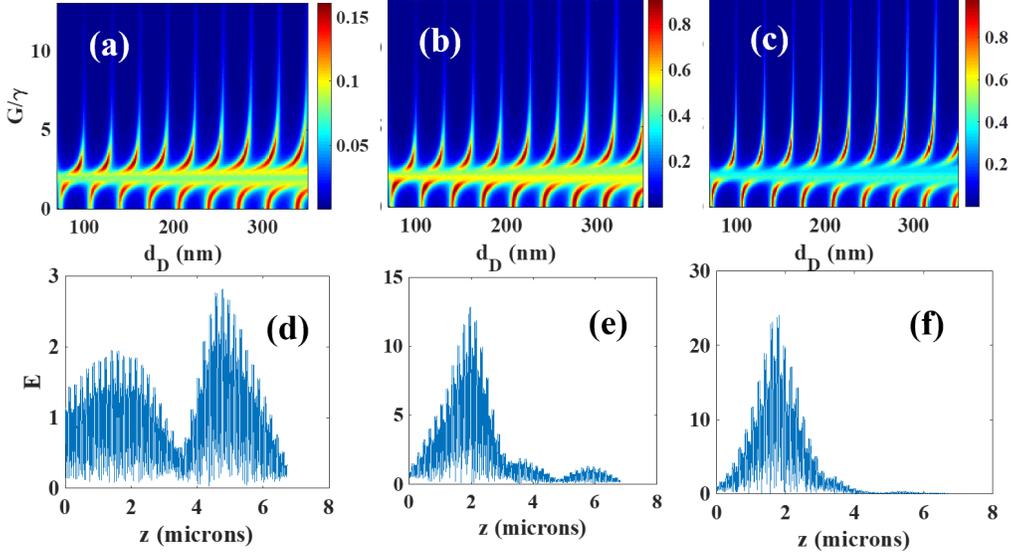


Figure 3: Absorption spectra for band edge mode as a function of control field, $\frac{G}{\gamma}$ and defect layer width d_D for different randomness parameter (a) $X = 10$ at $\omega = 2.2789 \times 10^{15} Hz$ (b) $X = 5$ at $\omega = 2.2525 \times 10^{15} Hz$ (c) $X = 2.5$ at $\omega = 2.2131 \times 10^{15} Hz$, and their corresponding electric field profiles along crystal axis, z respectively for layers, $n = 36$ at specific control field, G and defect layer width, d_D (d) $G = 2.809\gamma$, $d_D = 124.8744nm$, (e) $G = 0.71859\gamma$, $d_D = 209.2965nm$, and (f) $G = 1.1106\gamma$, $d_D = 74.2211nm$.

3.2. Variation of field profile

We further investigate the combined effects of randomness, LE, and absorption on the localization properties of disordered crystal with $2n+1$ layers, $n = 36$. We numerically plot electric field profiles corresponding to absorption and LE to obtain insights on localization across the length of PC.

We know for a crystal system, field decay for gap frequencies is $E(z) = E_0 \exp(-2z/L)$ and in the propagation region is $E(z) = E_0 \exp(-2z/L) \cos(kz)$, where $L^{-1} = L_{loc}^{-1} + L_{abs}^{-1}$, with L_{loc} , L_{abs} and k being the localization, absorption length due to inelastic scattering, and effective propagation vector respectively. In the literature, it has been commented that absorption due to inelastic scattering does not hinder the localization process, while it reduces the overall intensity of the field profile [21] and does not provide a cutoff length analogous to an inelastic scattering length [19].

In our study, we observe that localization within the band gap (de-

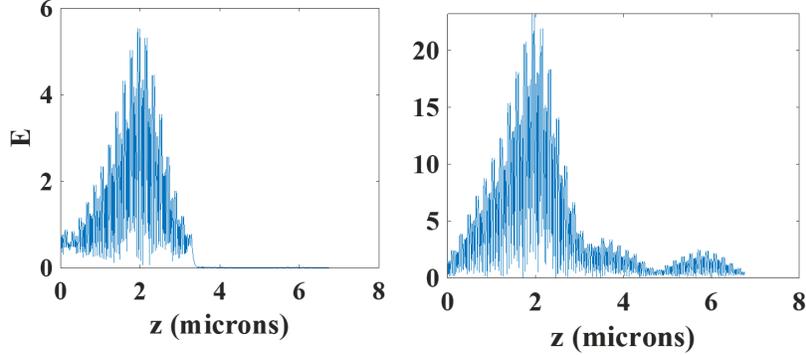


Figure 4: Electric field profile along crystal axis, z depicting localization pattern for different regions from Fig.3(b), the parameters are same as in Fig.3(b). (a) Yellow region, $G = 1.9\gamma$, $d_D = 150nm$ (b) Blue region, $G = 6\gamma$, $d_D = 150nm$.

fect modes) is significantly enhanced within the defect layer with increasing atomic absorption, while randomness suppresses this localization [Fig.2(d)-(f)]. Specifically, as the randomness parameter decreases from $X = 10$ (low disorder) to $X = 2.5$ (high disorder), the field intensity associated with defect modes is notably reduced in highly disordered PCs.

Conversely, at band edge frequencies, randomness induces more pronounced Anderson localization near the defect layer [Fig.3(d)-(f)]. For PCs with low disorder [Fig.3(d)], the field states exhibit uneven extensions. The oscillatory field profile is progressively dampened as disorder increases [Fig.3(e)and(f)]. This transition culminates in the emergence of Anderson localization, which evolves from weak to strong with increasing disorder. Further, we can also relate this type of localization with critical states (z^{-L}) that appeared in bandgap region with nonlinearity as control parameter as discussed in [16] but in that case system is made of non-linear Fibonacci multilayers. In contrast to the bandgap behavior, high absorption at band edge frequencies suppresses the field amplitude within the defect layer, consistent with observations reported in [21, 19].

Additionally, we analyze the field profile across different control field regions at band edge modes. In the high-absorption region (yellow region in Fig.3(b)), the field intensity rapidly decays upon reaching the defect layer, likely due to the combined effects of high Lyapunov exponent and absorption [Fig.4(a)]. As we transition toward regions with lower absorption with equidistant modes, the field profile becomes oscillatory though damped and

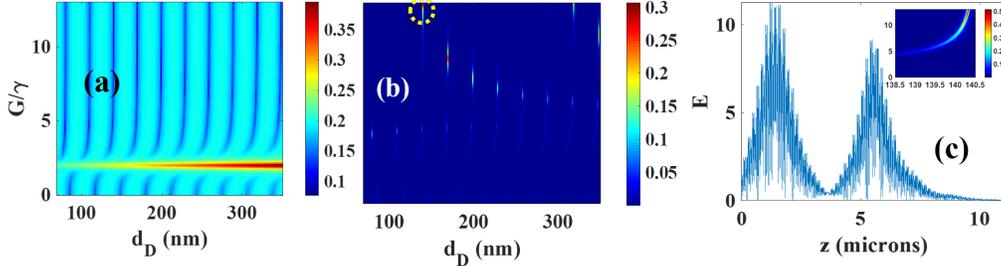


Figure 5: (a) Lyapunov exponent, (b) absorption spectra at $\omega = 2.3936 \times 10^{15} Hz$ as a function of control field, G and defect layer width, d_D and (c) field profile along crystal axis at $G = 13\gamma$, $d_D = 140.3518 nm$, inset depicts mode highlighted in yellow ring in (b), for $2n + 1$ number of layers, $n = 60$ at $X = 5$.

critical states arise [Fig.4(b)].

We have also analyzed the possibility of localization due to disorder and control field across the band gap region for crystal with $n = 60$. In Figs.5(a)-(c), the behaviour of LE, absorption, and electric field profile respectively is depicted at different gap frequency lying towards right band edge. While the behaviour of defect modes remains same as discussed above for $n = 36$ [Fig.2]. We want to emphasize that due to atomic doping, the occurrence of resonant modes is possible for the entire range of gap frequencies as a result of the control field even in the presence of disorder. So, the localization at the defect layer is enhanced due to the combined effect of absorption and LE [Fig.5(c)]. This trend is observed for $n=20, 36$ and 60 but all results are not shown. Inset in Fig.5(c) display high-resolution absorption plot corresponding to the red spot in Fig.5(b). This inset plot clearly indicates that the resonance spots are exceedingly delicate, a result of PC cavity's high Q factor. Hence, this study provides valuable insights into the switching of PC properties from strong to weak localization due to disorder. Moreover, it also supports the notion of coherent control of the mobility edge and localization across disordered PC. Furthermore, with penetration depths ranging from approximately $1 \mu m$ (for $n=20$) to nearly $11 \mu m$ (for $n=60$) [Fig.5(c)], this study opens up promising applications in biosensing focusing on sample surface interactions.

4. Conclusion

In this investigation, we explore the dynamic relationship between absorption, Lyapunov exponent, disorder, and localization phenomena in PCs

with tailored refractive index disorder in one of the bilayers. Our analysis revealed distinct localization mechanisms in band gap versus band edge regimes. Within the band gap, absorption strengthens field confinement, while increased disorder disrupts it. Conversely, near band edges, disorder-induced randomness enhances Anderson localization proximal to the defect layer, though excessive absorption attenuates this effect by damping field amplitudes within defect layer. Furthermore, we demonstrated that coherent control of LE, absorption and localization dynamics remains achievable through non-uniform doping of the defect layer with Λ -type atoms. This approach enables dynamic refractive index modulation, permitting precise tuning of mobility edge and selective switching between strong and weak localization states. Such capabilities highlight the potential for engineering surface-localized modes and adaptive photonic devices that harness disorder-coherence interplay. Future research directions could explore alternative doping geometries, heterogeneous material integration, or multi-layered disorder architectures to further enhance localization control.

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